PROCESS CPD92V

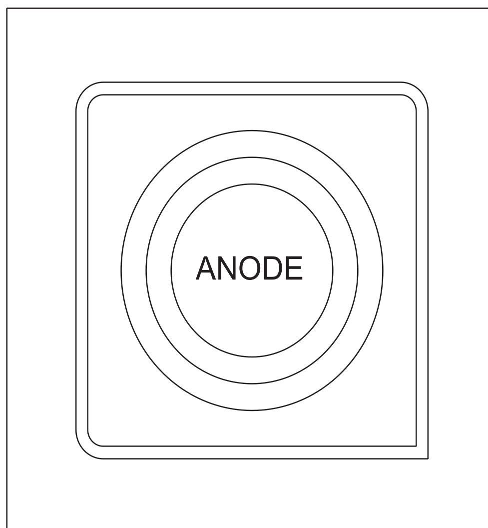
Schottky Diode

High Voltage Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.0 x 9.0 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	4.8 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER
139,050

PRINCIPAL DEVICE TYPES
CMDD6263
CMKD6263
CMLD6263 Series
CMOD6263
CMPD6263 SERIES
CMSD6263 SERIES
CMUD6263 Series
1N6263

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
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www.centralsemi.com

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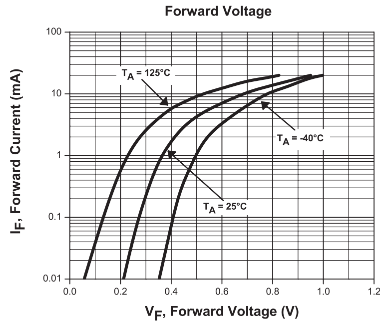
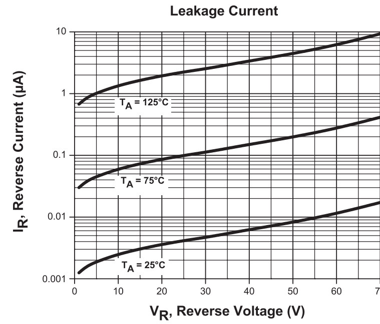
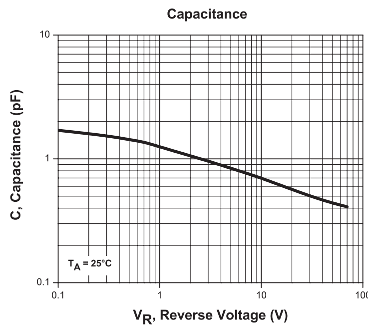
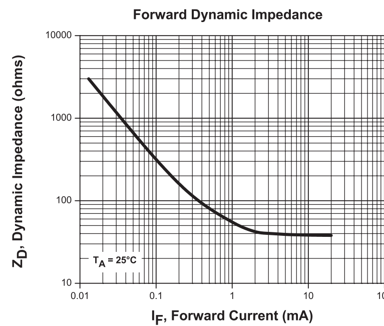
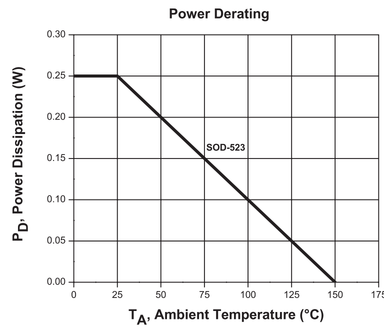
Typical Electrical Characteristics











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